Contents

Preface v

Organization vi

Primary Lecture

Thin films in the integrated circuit industry: requirements and deposition methods 1
E. H. A. Granneman (Bilthoven, Netherlands)

Molecular Beam and Atomic Layer Epitaxy

Reflection electron microscopy study of thin film growth 12
K. Yagi, H. Minoda and M. Shima (Tokyo, Japan)

In situ observation of the growth process of the InAs–GaAs heteroepitaxial system using scanning microprobe reflection high energy electron diffraction–total reflection angle X-ray spectroscopy 18
S. Shimizu, K. Yamamuro, K. Fuwa, H. Yanagida, H. Yamakawa (Kanagawa, Japan) and S. Ino (Tokyo, Japan)

Hydrogen cleaning of silicon wafers. Investigation of the wafer surface after plasma treatment 23
J. Ramm, E. Beck, A. Zueger (Balzers, Liechtenstein), A. Dommann (Buchs, Switzerland) and R. E. Pixley (Zürich, Switzerland)

Study of growth kinetics in silicon gas source molecular beam epitaxy with disilane using RHEED intensity oscillations 27
S. Butzke, K. Werner, J. Trommel, S. Radelaar and P. Balk (Delft, Netherlands)

Atomic force microscopy study of titanium dioxide thin films grown by atomic layer epitaxy 32
M. Ritala, M. Leskelä (Helsinki, Finland), L.-S. Johansson (Turku, Finland) and L. Niinistö (Espoo, Finland)

Growth and Structure of Thin Films

Thin film growth on an O-precovered Ru(0001) surface 36
K. Kalki, M. Schick, G. Ceballos and K. Wandelt (Bonn, Germany)

On the influence of the substrate properties on the internal growth stress of titanium films at 250 °C 40
H. J. Schneeweiß and R. Abermann (Innsbruck, Austria)

Properties and applications of vacuum-deposited Cu–Cr films 44
J. Schumann, W. Brückner and A. Heinrich (Dresden, Germany)

Vibrations at Ag–Au interfaces 49
E. V. Chulkov, I. Yu. Sklyadneva and G. G. Rusina (Tomsk, Russian Federation)

High rate sputtering of metals and metal oxides with a moving plasma zone 51
R. Kukla, M. Bähr, S. Beißwenger, W.-E. Fritsche and M. Lübbehusen (Hanau, Germany)

The influence of various process gases on the magnetron sputtering of ZrB_{12} 56
P. Losbichler, C. Mitterer (Loeben, Austria), W. S. M. Werner, H. Störi (Wien, Austria) and J. Barounig (Linz, Austria)

High resolution Rutherford backscattering spectroscopy studies on Mo/Si multilayers 60
B. Heidemann, T. Tappe, B. Schmiedeskamp and U. Heinzmann (Bielefeld, Germany)

Auger electron spectroscopy, low energy electron diffraction and electron energy loss spectroscopy studies of Se overlayers grown on Cu(111) surfaces 64
S. Nagashima and I. Ogura (Fukushima-ken, Japan)

Thin SiO_2–Si_3N_4–SiO_2 films: Auger depth profile evaluation by means of factor analysis 68
L. Gonzo, F. Marchetti and M. Sakar (Povo, Italy)

X-ray photoelectron spectroscopy and X-ray-excited Auger electron spectroscopy studies of the initial deposition of hydrogenated amorphous carbon 72
I. Montero, L. Galán (Madrid, Spain), A. Laurent, J. Perrière and J. Spousta (Paris, France)

Relation between the dislocations in chemically vapour-deposited diamond and the linewidth of the Raman spectrum . 76
M. Mitsuhashi, S. Karasawa, S. Ohya (Yokohama, Japan) and F. Togashi (Tokyo, Japan)

Characterization of a sputtered amorphous W–C–Co coating annealed in air 80
A. Cavaleiro and M. T. Vieira (Coimbra, Portugal)

Ion-assisted Film Growth: Mechanisms and Techniques

High bias sputtering for large-area selective deposition..... 87
C. Nender, I. V. Katardjiev, A. M. Barklund, S. Berg and P. Carlsson (Uppsala, Sweden)

Interface of a titanium film ion plated on stainless steel..... 91
H. Kibe, K. Yamada, M. Nagoshi, H. Noro, K. Sato (Kawasaki, Japan) and H. Kagechika (Tokyo, Japan)

Fundamental research on the deposition of cubic boron nitride films on curved substrates by ion-beam-assisted vapor deposition..... 97
M. Sueda, T. Kobayashi, H. Tsukamoto, T. Rokkaku, S. Morimoto, Y. Fukaya (Hiroshima, Japan), N. Yamashita and T. Wada (Yokohama, Japan)

Optical properties of Zr films grown under ion bombardment 100
J. F. Trigo, E. Elizalde and J. M. Sanz (Madrid, Spain)

Structures of Au and Ti thin films formed at the interface with Si by the plasma process 105
K. Kashiwagi, H. Sekiguchi and Y. Murayama (Kawagoe Saitama, Japan)

***In-situ* Analysis of Film Growth**

Effect of hydrogen dilution on the growth of hydrogenated amorphous silicon studied by *in-situ* phase-modulated ellipsometry 109
A. Canillas, J. Campmany, J. L. Andújar and E. Bertran (Barcelona, Spain)

Structure-dependent surface conductance at the initial stages in metal epitaxy on Si(111) surfaces..... 113
S. Hasegawa and S. Ino (Tokyo, Japan)

In and *ex situ* diagnostics of the growth of α-Ti thin films deposited by plasma-enhanced physical vapour deposition . 117
H. Steffen, H. Wulff (Greifswald, Germany) and A. Lunk (Stuttgart, Germany)

The oxidation kinetics of thin copper films studied by ellipsometry..... 121
M. Rauh and P. Wißmann (Erlangen, Germany)

Chemical vapour deposition tungsten film growth studied by *in situ* growth stress measurements..... 125
G. J. Leusink, T. G. M. Oosterlaken, G. C. A. M. Janssen and S. Radelaar (Delft, Netherlands)

Oxidation of silicon in r.f. plasma measured by rapid *in situ* during process ellipsometry..... 129
H. Shinno and M. Kitajima (Ibaraki, Japan)

Emission line intensities in an r.f. sputtering glow discharge system 133
J. L. Hernández-Rojas, M. L. Lucía, J. Santamaría, G. González-Díaz, I. Mártil and F. Sánchez-Quesada (Madrid, Spain)

In situ real-time ellipsometric study of the growth of r.f. plasma deposited amorphous hydrogenated silicon oxynitride thin films 137
J. Campmany, A. Canillas, J. L. Andújar, J. Costa and E. Bertran (Barcelona, Spain)

Compositionally Modulated Thin Films

H in Ti thin films..... 141
Th. Krist, M. Brière (Berlin, Germany) and L. Cser (Budapest, Hungary)

Excimer (XeCl) laser processing of W/Si bilayers and multilayers up to the Si melting threshold..... 145
E. D'Anna, M. L. De Giorgi (Lecce, Italy), S. Luby (Bratislava, Slovak Republic), A. Luches (Lecce, Italy), E. Majkova (Bratislava, Slovak Republic) and M. Martino (Lecce, Italy)

A study of thermally activated interfacial reactions in an Ni/Cr/Si multilayer structure 149
F. Pimentel (Stuttgart, Germany), A. Zalar (Ljubljana, Slovenia), S. Hofmann, D. Kohl (Stuttgart, Germany) and P. Punjan (Ljubljana, Slovenia)

Smoothing of interfaces in ultrathin Mo/Si multilayers by ion bombardment 154
A. Kloidt, H. J. Stock, U. Kleineberg, T. Döhring, M. Pröpper, B. Schmiedeskamp and U. Heinzmann (Bielefeld, Germany)

Interfacial reaction of MgO/TiO_x superlattice thin films 158
F. Imai, K. Kunimori, T. Uchijima and H. Nozoye (Ibaraki, Japan)

A study of thin Al films on Sn 162
R. A. Douglas, A. C. Peterlevitz and R. Landers (Campinas, Brazil)

Persistent photoconductivity in undoped a-Si:H/a-SiC:H multilayers 165
J. Bertomeu, J. Puigdollers, J. M. Asensi, J. Andreu and J. C. Delgado (Barcelona, Spain)

Preparation and microstructure of reactively sputtered $Ti_{1-x}Zr_xN$ films 169
I. Sakamoto, S. Maruno and P. Jin (Nagoya, Japan)

Superconducting Thin Films

Growth and structure of $YBa_2Cu_3O_{7-\delta}$ thin films studied by scanning tunnelling microscopy and electron microscopy . 173
H. Haefke, H. P. Lang, R. Sum, H.-J. Güntherodt (Basel, Switzerland) L. Berthold and D. Hesse (Halle, Germany)

High resolution electron microscopy on superconducting $YBa_2Cu_3O_7$ thin films 178
C. Træholt, J. G. Wen, V. Svetchnikov, A. Delsing and H. W. Zandbergen (Delft, Netherlands)

In-situ growth of epitaxial $YBa_2Cu_3O_7$ thin films by on-axis unbalanced d.c. magnetron sputtering 182
N. Savvides and A. Katsaros (Sydney, N.S.W., Australia)

Superconducting thin film thermometers for calorimetric particle detectors 186
W. Seidel (Munich, Germany)

Initial growth mechanism of Bi–Sr–Ca–Cu–O thin films on $SrTiO_3$(110) surfaces studied by *in-situ* reflection high energy electron diffraction observation 189
T. Miura and Y. Ishizuka (Kawasaki, Japan)

Laser deposition of Y–Ba–Cu–O on ZrO_2-coated sapphire substrates 193
A. J. Basovich, S. V. Gaponov (Nizhniy Novgorod, Russian Federation), L. Jastrabík, M. Jelínek (Prague, Czech Republic), N. A. Kiselev (Moscow, Russian Federation), E. B. Kluenkov (Nizhniy Novgorod, Russian Federation), O. I. Lebedov (Moscow, Russian Federation), L. A. Mazo (Nizhniy Novgorod, Russian Federation), L. Soukup (Prague, Czech Republic), M. D. Strikovskij, V. V. Talanov (Nizhniy Novgorod, Russian Federation) and A. L. Vasiliev (Moscow, Russian Federation)

Effects of carbon impurities in high T_c superconducting tapes using Auger electron spectroscopy 196
E. W. Seibt (Karlsruhe, Germany), A. Jeremie and R. Flükiger (Geneva, Switzerland)

Intrinsic pinning of vortices in superconducting Nb/Cu multilayers grown by molecular beam epitaxy 201
S. H. Brongersma, E. Verweij, N. J. Koeman, D. G. de Groot, R. Griessen (Amsterdam, Netherlands) and B. I. Ivlev (Moscow, Russian Federation)

Micromechanical Properties and Adhesion of Thin Films

The effect of surface aluminum oxide films on thermally induced hillock formation 205
C. Y. Chang and R. W. Vook (Syracuse, NY, USA)

Shape memory thin film of Ti–Ni formed by sputtering 210
A. Ishida, A. Takei (Meguroku, Japan) and S. Miyazaki (Tsukubashi, Japan)

Properties of reactively d.c.-magnetron-sputtered AlN thin films 215
E. Rille, R. Zarwasch and H. K. Pulker (Innsbruck, Austria)

Effect on lacquer adhesion of solid state properties of tin oxides 218
G. M. Ingo, G. Scavia and L. Giorgi (Rome, Italy)

Laser-damage threshold of Sc_2O_3/SiO_2 high reflector coatings for a laser wavelength of 355 nm 222
S. Tamura, S. Kimura, Y. Sato, H. Yoshida and K. Yoshida (Osaka, Japan)

Preparation and structure of Cu–W thin films 225
N. Radić, B. Gržeta, D. Gracin and T. Car (Zagreb, Croatia)

Texture and residual macrostress of Ti–N coatings 229
A. Gokhman (St. Petersburg, Russian Federation)

Physics and Chemistry of Wear-protective Films

Structural analysis of Zr–N and Ti–N films prepared by reactive plasma beam deposition 233
P. Panjan, B. Navinšek, A. Žabkar, V. Marinkovič, Dj. Mandrino and J. Fišer (Ljubljana, Slovenia)

Structure and properties of $(Ti_{1-x}Al_x)N$ films prepared by reactive sputtering 238
Y. Tanaka, T. M. Gür, M. Kelly, S. B. Hagstrom (Stanford, CA, USA) and T. Ikeda (Kobe, Japan)

Stress and anisotropy effects in the interfacial reactions of Al and TiN_x 242
F. Edelman, R. Brener, M. Eizenberg (Haifa, Israel), E. Sader and Y. Dafne (Jerusalem, Israel)

Transformation of titanium nitride in oxygen plasma 247
C. Jiménez (Madrid, Spain), J. Perrière (Paris, France), C. Palacio (Madrid, Spain), J. P. Enard (Paris, France) and J. M. Albella (Madrid, Spain)

Ion beam modification of the physical properties of MoS_x films 252
S. P. Kaye, H. Kheyrandish, J. S. Colligon (Salford, UK) and E. W. Roberts (Warrington, UK)

MoS_{2-x} lubricating films: structure and wear mechanisms investigated by cross-sectional transmission electron microscopy 257
J. Moser and F. Lévy (Lausanne, Switzerland)

Effect of plasma nitriding on the properties of (Ti,Al)N coatings deposited onto hot work steel substrates 261
T. Gredić, M. Zlatanović, N. Popović and Ž. Bogdanov (Belgrade, Yugoslavia)

High dose implantation of nitrogen in tool steel: Auger electron spectroscopy and hardness measurements 267
L. J. Bredell and J. B. Malherbe (Pretoria, South Africa)

Deposition of wear-resistant BN coatings by r.f. plasma-assisted chemical vapour deposition 272
J. Smeets, V. Van Den Bergh, J. Meneve, E. Dekempeneer and L. De Wilde (Mol, Belgium)

X-ray photoelectron spectroscopy and secondary-ion mass spectrometry of boron nitride thin films on austenitic stainless steel 276
G. M. Ingo and G. Padeletti (Rome, Italy)

Reactivity between Ti and N_2–C_2H_2 mixed gas on Ti(C,N) film deposition by arc-like plasma-enhanced ion plating .. 280
H. Kajioka, K. Higuchi (Kure, Japan) and Y. Kawashimo (Shiga, Japan)

Diamond Thin Films

Electron spin resonance study of diamond-like nuclei produced in an Si surface layer by high dose C ion doping 285
T. Izumi, Y. Show (Kanagawa, Japan), M. Deguchi, M. Kitabatake, T. Hirao, Y. Mori, T. Ito and A. Hiraki (Osaka, Japan)

Hardness and elastic modulus of diamond and diamond-like carbon films 289
N. Savvides and T. J. Bell (Sydney, N.S.W., Australia)

Calculations for defects formed on diamond surfaces 293
T. Halicioglu (Stanford, CA, USA)

X-ray study of silicon distortion on deposition of diamond-like films 297
V. Chaplanov, I. Galkin, A. Nefedov, I. Shipov, S. Yakimov, S. Gerasimovich, V. Elinson and V. Sleptsov (Moscow, Russian Federation)

Polymeric Thin Films

Morphology of thin polyimide films 301
G. Danev, E. Spassova and K. Popova (Sofia, Bulgaria)

Study of ultrafine particles–organic polymer thin films 304
Z. Q. Xue, W. M. Liu, Y. W. Liu, H. J. Gao, X. Y. Zhao, Q. D. Wu, S. J. Pang, C. Zhu, Z. Ma and J. Shen (Beijing, People's Republic of China)

Low temperature plasma treatment of monomolecular Langmuir–Blodgett films 307
A. A. Kalachev, K. Mathauer, U. Höhne, H. Möhwald and G. Wegner (Mainz, Germany)

Film Growth Kinetics and Computer Modelling

Area-selective CVD of metals 312
K. Tsubouchi and K. Masu (Sendai, Japan)

Modelling and computer simulation of ion-beam- and plasma-assisted film growth 319
W. Möller (Garching, Germany)

Atomic-scale simulation of interface defect formation in the initial stages of thin film growth 326
M. D. Rouhani, A. M. Gué, M. Sahlaoui and D. Estève (Toulouse, France)

Computer simulation of growth of thin films fabricated by the sputtering method: comparison with experiment 330
K. Nanbu, S. Uchida (Sendai, Japan) and H. Yoshida (Tokyo, Japan)

Author Index 333

Subject Index 335